IEEE SW Test Workshop Semiconductor Wafer Test Workshop

> June 7-10, 2009 San Diego, CA



Evaluation of Low Pressure MEMS Probes

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Process. Control. Yield.

Outline

- Design Review
 - Specifications
 - Resultant Design
- Design Evaluation
 - Force vs deflection
 - Life Tests
 - Scrub
- Conclusion



Design Specification

- User replaceable
 probes
- Compatible with existing technology
- Reliable solution
- Chose a buckling beam type design
- Precision ceramics









Surface Roughness of Inner Hole Wall



Upper Die Measurements







Lower Die Measurements



Mechanical drilling of machinable ceramic



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Buckling Beam Review



Hi Cu Li O

High Stress Concentrations Limit Force and Overdrive



Coined from wire

Coined from a slender wire. Bending in curved section



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Observations Regarding Standard Buckling Beam Probes Spring rate of probe is driven by - Length and offset of coined section - Width of coined section Stress concentrations - Transitions - Micro-hole constraints Pitch Limitation – Wire size - Cross-sectional length of coined section June 7 to 10, 2009 IEEE SW Test Workshop 10

MEMs Probe Design

Design Constraints

- Multiple layer photolithographic & plating process
- Minimize layer count
- Maximum stress less than ½ ultimate strength at greater than 5mil OD
- Minimize cross-section for fine pitch applications



Final Design

Long slender probe

- Three layers
 - Fine pitch (less than 60um)
 - Lower production costs
- Stress concentration
 - Limits spring rate
- Low BCF
 - 1.0 to 1.5 gm from 50um to 75um OD
 - Maximum 2.0 gm





Probe Tip Contact Force



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Will Low Force Work?

• Build test vehicle

- Fully functional
- 60um pitch

• Evaluate

- Life time contact resistance
- Scrub
 - Depth
 - Alignment



MEMs Probes



- Unique probe tip geometry
- Superior material properties
- Prime manufacturing tolerances



Test Procedure

Wafer scrub analysis

- Scrub wafer at 50um and 75um overdrive
- Measure scrub position and depth with WaferWoRx 300

CRES as a function of touch downs

- Measure test vehicle path resistance with PRVxII
- Scrub on wafer multiple times at 50um overdrive
- Periodically remeasure path resistance with PRVxII



- Scrub wafer at 50um and 75um OD
- Use WaferWoRx 300 system
 - Measure scrub depth profiles
 - Measure scrub position











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Summary of Readings

- Scrub depth 0.18um ± 0.03um (one sigma)
- Scrub length 15um ± 7um (one sigma)
- Scrub width 12um ± 4um (one sigma)
- Scrub alignment 7um ± 4um (one sigma)

Comments:

All measurements at 75um OD Probe tip width 8um Rejected alignment outliers



Life Testing: CRES





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Conclusion

- Design constraints led to low force probe design with maximum force of ~2gm
- Probe penetrates wafer .18um for 75um OD yielding good wafer contact
- Small probe tip contact with hard plated metal yields low, consistent, and stable CRES
- Path resistance drops to less than 2 Ohms when probing aluminum wafer
- New drill technology and machinable ceramic material aids in improved alignment accuracy



Acknowledgements

Rod Doe

- Senior Engineer
- Rudolph Technologies
- Shoichi Asanuma
 - TOTO Advanced Ceramics
- Additional data regarding hard ceramics will be presented during Wednesday morning session

